

## CLAIMS

What is claimed is:

- 1 1. A method, comprising:
  - 2 applying an adhesive gel material to at least a portion of a first side of a
  - 3 semiconductor wafer having first and second sides;
  - 4 positioning the semiconductor wafer on to a platform with the first side
  - 5 facing the platform and with the adhesive gel material between the first side and
  - 6 the platform to allow the adhesive gel material to hold the semiconductor wafer to
  - 7 the platform;
  - 8 grinding the second side of the semiconductor wafer; and
  - 9 allowing the adhesive gel material to release the semiconductor wafer
- 10 from the platform.
- 1 2. The method of claim 1 wherein allowing the adhesive gel material to hold
- 2 the semiconductor wafer to the platform comprises using an adhesive property of
- 3 the adhesive gel material to hold the semiconductor wafer to the platform.
- 1 3. The method of claim 2, wherein the platform includes a vacuum, and
- 2 wherein using the adhesive property to hold the semiconductor wafer to the
- 3 platform includes holding the semiconductor wafer in position using the adhesive
- 4 gel material with the vacuum substantially turned off.
- 1 4. The method of claim 2 wherein using the adhesive property to hold the
- 2 semiconductor wafer to the platform includes providing substantial surface
- 3 contact between the adhesive gel material and the first side of the wafer.

1       5.     The method of claim 1, wherein allowing the adhesive gel material to  
2 release the semiconductor wafer from the platform includes applying a vacuum to  
3 the gel material to substantially pull the adhesive gel material off the first side of  
4 the semiconductor wafer.

1       6.     The method of claim 1 wherein applying the adhesive gel material to at  
2 least a portion of the first side of the semiconductor wafer includes applying the  
3 adhesive gel material to an upper surface of an un-diced semiconductor wafer.

1       7.     The method of claim 6, further comprising after grinding the second side of  
2 the semiconductor wafer, which comprises a lower surface of the semiconductor  
3 wafer:

4              washing the semiconductor wafer;  
5              mounting the semiconductor wafer; and  
6              dicing the semiconductor wafer.

1       8.     The method of claim 1, wherein applying the adhesive gel material to the  
2 first side of the semiconductor wafer includes applying the adhesive gel material  
3 to an upper surface of at least a partially-diced semiconductor wafer.

1       9.     The method of claim 8, further comprising after grinding the second side of  
2 the semiconductor wafer, which comprises a lower surface of the semiconductor  
3 wafer, mounting the semiconductor wafer that has had its lower surface grinded.

1       10.    The method of claim 1, wherein applying the adhesive gel material to the  
2 first side of the semiconductor wafer includes applying the adhesive gel material  
3 to an upper surface of a flip chip bump wafer or non-bump wafer

1    11.    The method of claim 1 wherein applying the adhesive gel material  
2    includes applying a gel material including semi-solid particles.

1    12.    The method of claim 11 wherein allowing the adhesive gel material to  
2    release the semiconductor wafer from the platform includes applying a vacuum to  
3    draw the membrane away from the first side of the semiconductor wafer

1    13.    The method of claim 1 wherein applying the adhesive gel material to the  
2    first side of the semiconductor wafer includes applying the adhesive gel material  
3    to an upper surface of a semiconductor wafer having surface structures.

1    14.    The method of claim 13 wherein the surface structures include bumps.

1    15.    The method of claim 13 wherein the surface structures include electronic  
2    circuitry.

1    16.    A method, comprising:

2                applying a gel material to a first side of a semiconductor wafer, having first  
3    and second sides, to provide substantial surface contact between the gel  
4    material and surface structures on the first side;

5                placing the wafer on a vacuum chuck with the gel material between the  
6    wafer and the vacuum chuck;

7                grinding the second side while using the gel material to hold the wafer  
8    against the vacuum chuck; and

9                removing the wafer from the vacuum chuck by reducing surface contact  
10   between the gel material and the surface structures.

1    17.   The method of claim 16, wherein applying the gel material to the first side  
2    of the semiconductor wafer includes applying the gel material to a surface of at  
3    least one of a flip-chip bump wafer and a non-bump wafer.

1    18.   The method of claim 16 wherein the surface structures comprise  
2    electronic circuitry.

1    19.   The method of claim 16 wherein the surface structures comprise bumps.

1    20.   The method of claim 16 wherein reducing surface contact between the gel  
2    material and the surface structures includes activating the vacuum chuck.

1    21.   The method of claim 16 wherein the gel material includes semi-solid  
2    particles.

1    22.   The method of claim 16 wherein applying the gel material to the first side  
2    of the wafer includes applying a semi-solid material to an upper surface of the  
3    wafer, the semi-solid material capable to prevent substantial collapse of a gel  
4    membrane of the gel material into the vacuum chuck.

1    23.   The method of claim 16, further comprising after removing the wafer from  
2    the vacuum chuck:

- 3            washing the wafer;
- 4            mounting the wafer; and
- 5            dicing the wafer.

- 1    24.    The method of claim 16, further comprising dicing the wafer before
- 2    applying the gel material to the first side of the wafer.
  
- 1    25.    The method of claim 24 wherein the wafer is diced to a depth deeper than
- 2    a final desired depth of the wafer.
  
- 1    26.    The method of claim 16, further comprising using a vacuum transfer
- 2    device to transfer the wafer from the vacuum chuck onto a surface for mounting.
  
- 1    27.    The method of claim 16 wherein grinding the second side of the wafer
- 2    while using the gel material to hold the wafer against the vacuum chuck includes
- 3    absorbing at least some of a grinding force applied to the second side of the
- 4    wafer.
  
- 1    28.    A material, comprising:
  - 2        an adhesive gel material;
  - 3        semi-solid particles within the adhesive gel material; and
  - 4        wherein the adhesive gel material forms a membrane surface to hold a
  - 5        first side of a semiconductor wafer to a surface of a vacuum chuck during wafer
  - 6        grinding of a second side of the semiconductor wafer.
  
- 1    29.    The material of claim 28 wherein the semi-solid particles within the
- 2    adhesive gel material form a structure to substantially prevent the membrane
- 3    surface from collapsing to the surface of the vacuum chuck when the vacuum
- 4    chuck is activated.

1    30. The material of claim 28 wherein the semi-solid particles within the  
2 adhesive gel material includes organic particles.